CPH3355

Power MOSFET –30V, 156mΩ, –2.5A, Single P-Channel



Features

- On-resistance $R_{DS}(on)1=120m\Omega$ (typ)
- 4V drive
- Halogen free compliance

Specifications

Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	-30	V
Gate to Source Voltage	VGSS	±20	V
Drain Current (DC)	ID	-2.5	А
Drain Current (Pulse) PW≤10μs, duty cycle≤1%	IDP	-10	А
Power Dissipation When mounted on ceramic substrate (900mm ² ×0.8mm)	PD	1.0	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

This product is designed to "ESD immunity < 200V*", so please take care when handling. * Machine Model

Thermal Resistance Ratings

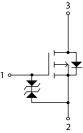
Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (900mm ² ×0.8mm)	R _{θJA}	125	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

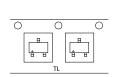
ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

Electrical Connection P-Channel







Packing Type:TL

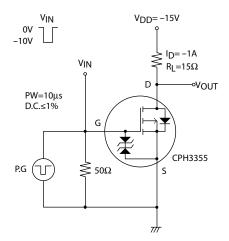


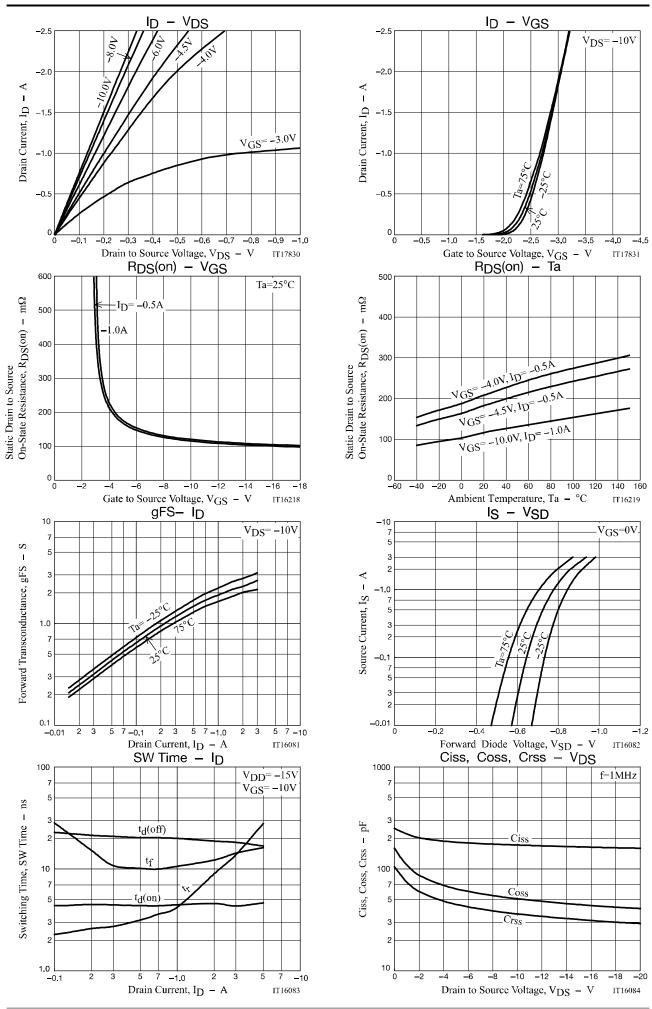
Electrical Characteristics at $Ta = 25^{\circ}C$

Parameter	Symbol Conditions	Que ditions		Value		
Parameter		min	typ	max	Unit	
Drain to Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-30			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-30V, V _{GS} =0V			-1	μΑ
Gate to Source Leakage Current	IGSS	$V_{GS}=\pm 16V, V_{DS}=0V$			±10	μΑ
Gate Threshold Voltage	VGS(th)	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transconductance	9FS	V _{DS} =-10V, I _D =-1A		1.9		S
	R _{DS} (on)1	I _D =-1A, V _{GS} =-10V		120	156	mΩ
Static Drain to Source On-State Resistance	R _{DS} (on)2	I _D =-0.5A, V _{GS} =-4.5V		187	262	mΩ
	R _{DS} (on)3	I _D =-0.5A, V _{GS} =-4V		213	299	mΩ
Input Capacitance	Ciss	V _{DS} =-10V, f=1MHz		172		pF
Output Capacitance	Coss			51		pF
Reverse Transfer Capacitance	Crss			36		pF
Turn-ON Delay Time	t _d (on)			4.5		ns
Rise Time	tr			4.2		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		20		ns
Fall Time	tf			10.6		ns
Total Gate Charge	Qg	V _{DS} =-15V, V _{GS} =-10V, I _D =-2.5A		3.9		nC
Gate to Source Charge	Qgs			0.6		nC
Gate to Drain "Miller" Charge	Qgd			0.8		nC
Forward Diode Voltage	V _{SD}	IS=-2.5A, VGS=0V		-0.86	-1.5	V

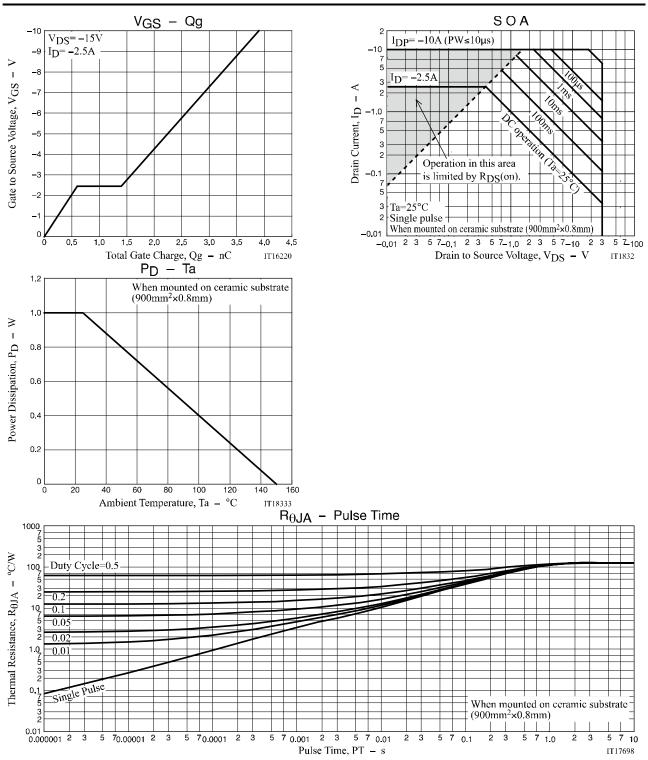
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit





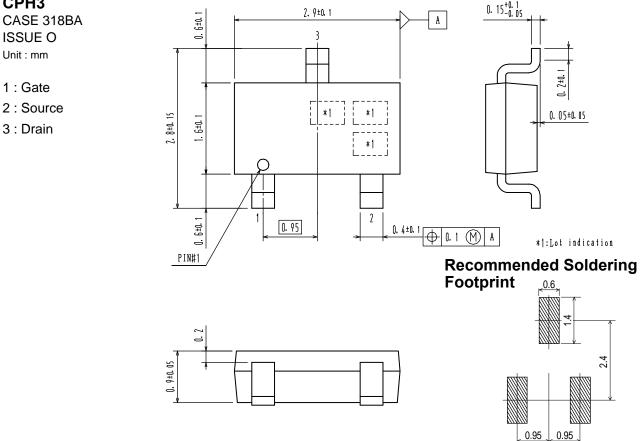
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Package Dimensions

CPH3355-TL-H/ CPH3355-TL-W

CPH3



ORDERING INFORMATION

Device	Package	Shipping	Note
CPH3355-TL-H	CPH3, SC-59	3,000	Pb-Free
CPH3355-TL-W	SOT-23, TO-236	pcs. / reel	and Halogen Free

Note on usage : Since the CPH3355 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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